



SUD08P06-155L-E3 Information



For Reference Only

Part Number SUD08P06-155L-E3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 60V 8.4A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SUD08P06-155L-E3 Specifications

Manufacturer Part Number SUD08P06-155L-E3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 8.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 450PF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C8.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs155 mOhm @ 5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	TrenchFET?
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Current - Continuous Drain (Id) @ 25°C Brive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 8.4A (Tc) 8.4C (10) 8.4C (10) 8	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs155 mOhm @ 5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	8.4A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 450pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 450pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max) $\pm 20 \text{V}$ FET Feature-Power Dissipation (Max) 2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs 155 mOhm @ $5A$, 10V Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C}$ (TJ)Mounting TypeSurface MountSupplier Device Package $TO-252$, $(D-Pak)$ Package / Case $TO-252-3$, $DPak$ ($2 \text{ Leads} + Tab$), $3 \text{ SC} -63$	Gate Charge (Qg) (Max) @ Vgs	19nC @ 10V
FET Feature - Power Dissipation (Max) 2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	450pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 155 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	2W (Ta), 25W (Tc)
Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	155 mOhm @ 5A, 10V
Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252, (D-Pak)
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

SUD08P06-155L-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SUD08P06-155L-E3 Payment Methods









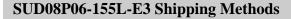
























If you have any question about SUD08P06-155L-E3, please do not hesitate to contact us!

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